

Isc N-Channel MOSFET Transistor

SPA08N80C3

• FEATURES

- With TO-220F package
- Low input capacitance and gate charge
- Reduced switching and conduction losses
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

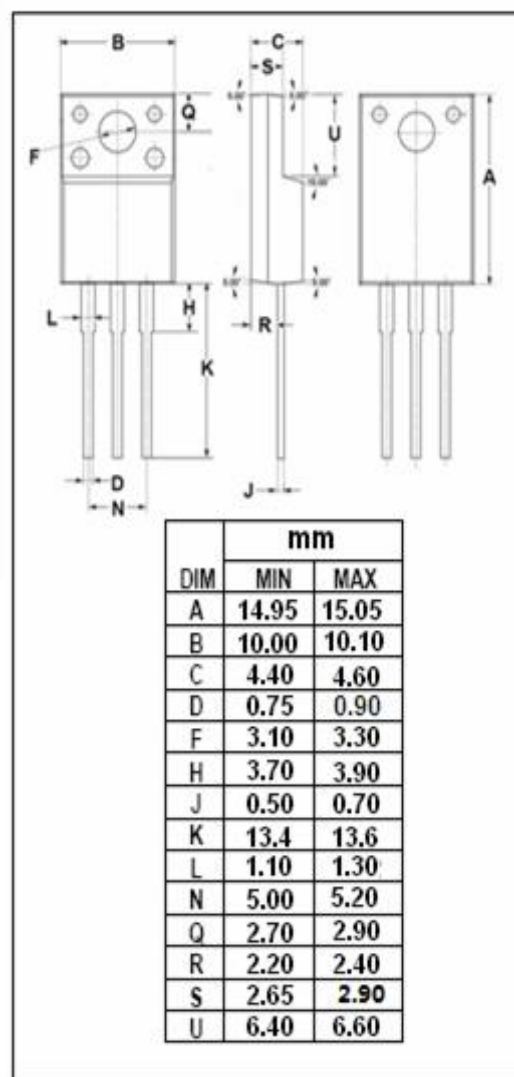
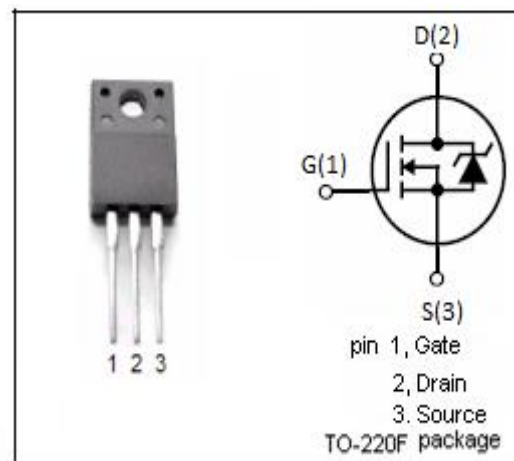
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	800	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous @ $T_c=25^{\circ}\text{C}$ (V_{GS} at 10V) $T_c=100^{\circ}\text{C}$	8 5.1	A
I_{DM}	Drain Current-Single Pulsed	24	A
P_D	Total Dissipation @ $T_c=25^{\circ}\text{C}$	40	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	3.8	$^{\circ}\text{C/W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	80	$^{\circ}\text{C/W}$



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ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=0.25mA$	800			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.47mA$	2.1		3.9	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=5.1A$		560	650	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=800V; V_{GS}=0V; T_J=25^{\circ}\text{C}$ $V_{DS}=800V; V_{GS}=0V; T_J=150^{\circ}\text{C}$			1 100	μA
V_{SDF}	Diode forward voltage	$I_{SD}=8A, V_{GS}=0V$		1.0	1.2	V